

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

2N2369A T0-18 CASE
2N5769 T0-92 CASE (EBC)
PN2369A T0-92 CASE (EBC)

NPN SILICON TRANSISTORS

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N2369A, 2N5769, PN2369A types are silicon NPN epitaxial planar transistors designed for ultra high speed saturated switching applications.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL	2N2369A	2N5769 PN2369A	UNIT
Collector-Base Voltage	V _{CB0}	40	40	V
Collector-Emitter Voltage	V _{CES}	40	40	V
Collector-Emitter Voltage	V _{CEO}	15	15	V
Emitter-Base Voltage	V _{EBO}	4.5	4.5	V
Collector Current	I _C	200	200	mA
Collector Current (PEAK)	I _{CM}	500	500	mA
Power Dissipation	P _D	360	625	mW
Power Dissipation (T _C =25°C)	P _D	1.2	1.5	W
Operating and Storage Junction Temperature (T0-18)	T _J , T _{STG}	-65 TO +200		°C
Operating and Storage Junction Temperature (T0-92)	T _J , T _{STG}	-65 TO +150		°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _{CBO}	V _{CB} =20V		400	nA
I _{CBO}	V _{CB} =20V, T _A =150°C (2N2369A ONLY)		30	μA
BV _{CB0}	I _C =10μA	40		V
BV _{CES}	I _C =10μA	40		V
BV _{CEO}	I _C =10mA	15		V
BV _{EBO}	I _E =10μA	4.5		V
V _{CE} (SAT)	I _C =10mA, I _B =1.0mA		0.20	V
V _{CE} (SAT)	I _C =10mA, I _B =1.0mA, T _A =125°C (2N2369A ONLY)		0.30	V
V _{CE} (SAT)	I _C =30mA, I _B =3.0mA		0.25	V
V _{CE} (SAT)	I _C =100mA, I _B =10mA		0.50	V
V _{BE} (SAT)	I _C =10mA, I _B =1.0mA	0.70	0.85	V
V _{BE} (SAT)	I _C =30mA, I _B =3.0mA		1.15	V
V _{BE} (SAT)	I _C =100mA, I _B =10mA		1.60	V
h _{FE}	V _{CE} =0.35V, I _C =10mA	40	120	
h _{FE}	V _{CE} =0.35V, I _C =10mA, T _A =-55°C (2N2369A ONLY)	20		
h _{FE}	V _{CE} =0.40V, I _C =30mA	30		
h _{FE}	V _{CE} =1.0V, I _C =100mA	20		
f _T	V _{CE} =10V, I _C =10mA, f=100MHz	500		MHz
C _{ob}	V _{CB} =5.0V, I _E =0, f=140kHz		4.0	pF
t _{ON}	V _{CC} =3.0V, I _C =10mA, I _{B1} =3.0mA		12	ns
t _{OFF}	V _{CC} =3.0V, I _C =10mA, I _{B1} =3.0mA, I _{B2} =-1.5mA		18	ns
τ _s	V _{CC} =10V, I _C =10mA, I _{B1} =I _{B2} =10mA		13	ns

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